



SGS-THOMSON
MICROELECTRONICS

BU921ZP/ZPFI
BU921ZT/ZTFI

SGS-THOMSON

3DE D

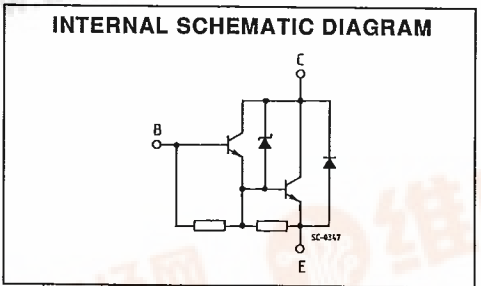
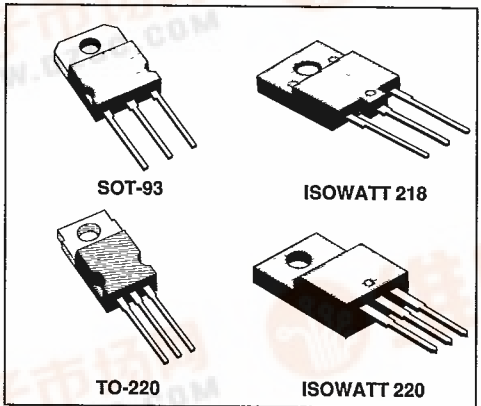
NPN POWER DARLINGTON

ADVANCE DATA

- HIGH RUGGEDNESS
- INTEGRATED HIGH VOLTAGE ZENER

AUTOMOTIVE MARKET

- APPLICATION IN HIGH PERFORMANCE ELECTRONIC CAR IGNITION



DESCRIPTION

The BU921ZP, BU921ZT, BU921ZPFI and BU921ZTFI are silicon multiepitaxial biplanar NPN transistors in monolithic darlington configuration mounted respectively in SOT-93, TO-220 plastic packages and ISOWATT218, ISOWATT220 fully isolated packages.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit			
V_{CBO}	Collector-base Voltage ($I_E = 0$)	350	V			
V_{CER}	Collector-emitter Voltage ($R_{BE} = 100 \Omega$)	350	V			
V_{CES}	Collector-emitter Voltage ($V_{BE} = 0$)	350	V _r			
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	350	V			
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	5	V			
I_C	Collector Current	16	A			
I_B	Base Current	5	A			
P_{tot}	Total Dissipation at $T_o < 25^\circ C$	SOT-93	ISOWATT218	TO-220	ISOWATT220	W
T_{stg}		125	60	100	40	
T_j	Storage Temperature	- 40 to 150				$^\circ C$
	Max. Operating Junction Temperature	150				$^\circ C$

THERMAL DATA **S G S-THOMSON** **30E D**

			SOT-93	ISOWATT218	TO-220	ISOWATT220	
$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	1	2.08	1.25	3.12	°C/W

T-33-29

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 350\text{ V}$			250	μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{BE} = -5\text{ V}$			50	mA
V_{CL}	Clamping Voltage	either $I_B = 0$ or $V_{BE} = 0$ and $I_C = 100\text{ mA}$ same $T_j = 125\text{ °C}$	350 350		500 500	V V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 5\text{ A}$ $I_B = 50\text{ mA}$ $I_C = 6\text{ A}$ $I_B = 75\text{ mA}$ $I_C = 8\text{ A}$ $I_B = 120\text{ mA}$ $T_j = 125\text{ °C}$ $I_C = 5\text{ A}$ $I_B = 50\text{ mA}$ $I_C = 6\text{ A}$ $I_B = 75\text{ mA}$ $I_C = 8\text{ A}$ $I_B = 120\text{ mA}$		1.03 1.08 1.17 0.98 1.04 1.17	1.4 1.5 1.6	V V V V V V
$V_{BE(sat)}^*$	Base-emitter Saturation Voltage	$I_C = 6\text{ A}$ $I_B = 75\text{ mA}$ $I_C = 8\text{ A}$ $I_B = 120\text{ mA}$			2.2 2.3	V V
h_{FE}	DC Current Gain	$I_C = 5\text{ A}$ $V_{CE} = 10\text{ V}$	300			
V_F^*	Diode Forward Voltage	$I_F = 10\text{ A}$			2.5	V
	USE TEST	$V_{CC} = 24\text{ V}$ $L = 8\text{ mH}$	8			A

* Pulsed : pulsed duration = 300 μs , duty cycle = 1.5 %.